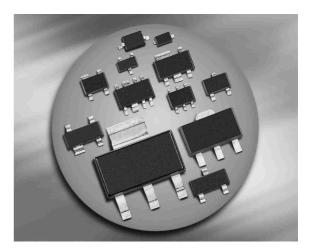


Silicon Variable Capacitance Diode

- For VHF TV / VTR tuners
- Pb-free (RoHS compliant) package





BB640



| Туре | Package | Configuration | L _S (nH) | Marking |
|-------|---------|---------------|---------------------|---------|
| BB640 | SOD323 | single | 1.8 | red S |

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

| Parameter | Symbol | Value | Unit | |
|---------------------------------|------------------|---------|------|--|
| Diode reverse voltage | V _R | | V | |
| Peak reverse voltage | V _{RM} | 35 | | |
| ($R \ge 5 \mathrm{k} \Omega$) | | | | |
| Forward current | I _F | 20 | mA | |
| Operating temperature range | T _{op} | -55 150 | °C | |
| Storage temperature | T _{stg} | -55 150 | | |



| Parameter | Symbol | Values | | | Unit |
|---|-----------------------------------|--------|------|------|------|
| | | min. | typ. | max. |] |
| DC Characteristics | | | | | |
| Reverse current | I _R | | | | nA |
| <i>V</i> _R = 30 V | | - | - | 10 | |
| <i>V</i> _R = 30 V, <i>T</i> _A = 85 °C | | - | - | 200 | |
| AC Characteristics | | | | | |
| Diode capacitance | CT | | | | pF |
| V _R = 1 V, <i>f</i> = 1 MHz | | 62 | 69 | 76 | |
| V _R = 2 V, <i>f</i> = 1 MHz | | 47.5 | 54.5 | 61.5 | |
| V _R = 25 V, <i>f</i> = 1 MHz | | 2.85 | 3.28 | 3.7 | |
| V _R = 28 V, <i>f</i> = 1 MHz | | 2.8 | 3.05 | 3.3 | |
| Capacitance ratio | C _{T1} /C _{T28} | 19.5 | - | 25 | |
| V _R = 1 V, V _R = 28 V, <i>f</i> = 1 MHz | | | | | |
| Capacitance ratio | C _{T2} /C _{T25} | 15 | 16.6 | - | |
| V _R = 2 V, V _R = 25 V, <i>f</i> = 1 MHz | | | | | |
| Capacitance matching ¹⁾ | $\Delta C_{T}/C_{T}$ | - | - | 2.5 | % |
| $V_{\rm R}$ = 1 V, $V_{\rm R}$ = 28 V, f = 1 MHz | | | | | |
| Series resistance | r _S | - | 1.15 | - | Ω |
| C _T = 12 pF, <i>f</i> = 100 MHz | | | | | |

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

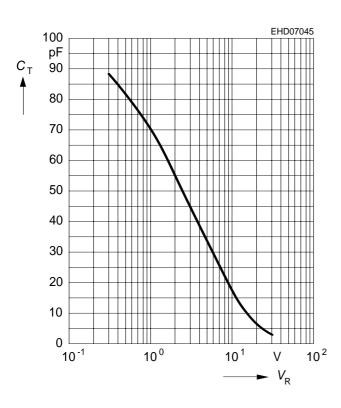
¹For details please refer to Application Note 047.



BB640...

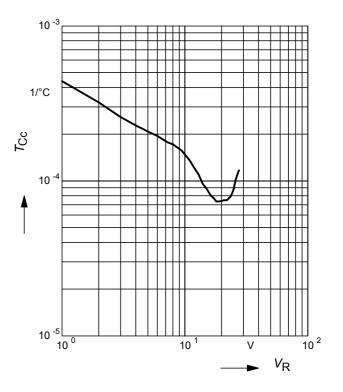
Diode capacitance $C_{T} = f(V_{R})$

f = 1 MHz

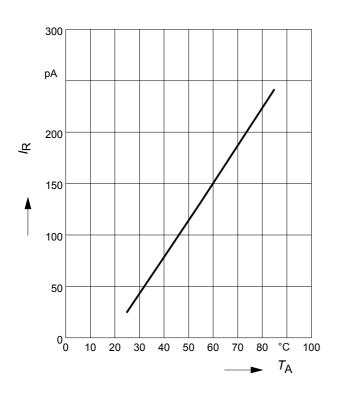


Temperature coefficient of the diode

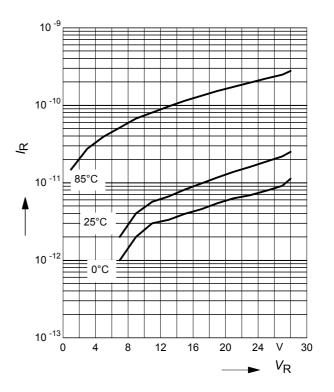
capacitance $T_{Cc} = f(V_R)$



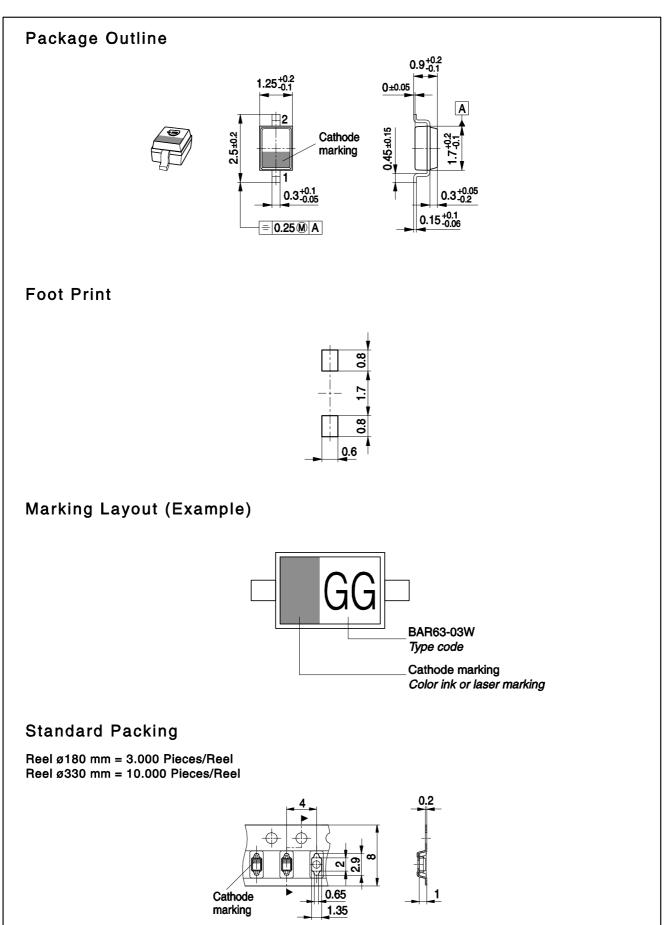
Reverse current $I_R = f(T_A)$ $V_R = 28V$



Reverse current $I_{R} = f(V_{R})$ T_{A} = Parameter









Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

© 2009 Infineon Technologies AG All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (<<u>www.infineon.com</u>>).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.